
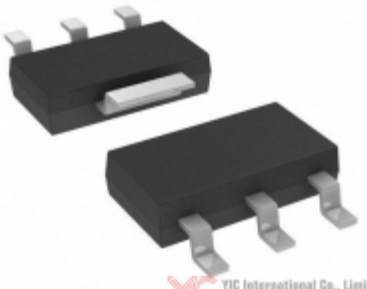










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|---|--------------------------------|--|
|  | FDT55AN06LA0 | |
| | Hersteller-Teilenummer: | FDT55AN06LA0 |
|  | Hersteller / Marke: | Fairchild/ON Semiconductor |
| | Teil der Beschreibung: | MOSFET N-CH 60V 12.1A SOT223-4 |
| <p>Image may be representation. See specs for product details.</p> | Datenblätter: | 1.FDT55AN06LA0.pdf 2.FDT55AN06LA0.pdf |
| | RoHs Status: | Bleifrei / RoHS-konform |
| | Lagerzustand: | New original, 24146 pcs Stock Available. |
| | Liefern von: | Hong Kong |
| | Versandweg: | DHL/Fedex/TNT/UPS/EMS |

Spezifikationen

| | |
|---|--|
| Teilenummer | FDT55AN06LA0 |
| Hersteller | Fairchild/ON Semiconductor |
| Beschreibung | MOSFET N-CH 60V 12.1A SOT223-4 |
| Kategorie | Diskrete Halbleiterprodukte > Transistoren-FETs, |
| Teilstatus | 24146 pcs Stock |
| Serie | PowerTrench® |
| Technologie | MOSFET (Metal Oxide) |
| Betriebstemperatur | -55°C ~ 150°C (TJ) |
| Befestigungsart | Surface Mount |
| Verpackung / Gehäuse | TO-261-4, TO-261AA |
| Supplier Device-Gehäuse | SOT-223-4 |
| Verlustleistung (max) | 8.9W (Tc) |
| Typ FET | N-Channel |
| FET-Merkmal | - |
| Drain-Source-Spannung (Vdss) | 60V |
| Strom - Ununterbrochener Abfluss (Id) bei 25 °C | 12.1A (Tc) |
| Rds On (Max) @ Id, Vgs | 46 mOhm @ 11A, 10V |
| VGS (th) (Max) @ Id | 3V @ 250µA |
| Gate Charge (Qg) (Max) @ Vgs | 10nC @ 10V |
| Eingabekapazität (Ciss) (Max) @ Vds | 1130pF @ 25V |
| Verpackung | Tape & Reel (TR) |

FDT55AN06LA0 ist neu im Original, Suche FDT55AN06LA0 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie FDT55AN06LA0 Fairchild/ON Semiconductor mit Garantie und Vertrauen. Anfrage FDT55AN06LA0: Info@Y-IC.com

Sie können auch interessiert sein:

| | | | |
|---|---|---|---|
|  <p>FDT86106LZ AMI Semiconductor / ON Semiconductor MOSFET N-CH 100V 3.2A SOT-223-4</p> |  <p>FDT461N Fairchild/ON Semiconductor MOSFET N-CH 100V 0.54A SOT-223</p> |  <p>FDT55AN06LA0 AMI Semiconductor / ON Semiconductor MOSFET N-CH 60V 12.1A SOT223-4</p> |  <p>FDT459N AMI Semiconductor / ON Semiconductor MOSFET N-CH 30V 6.5A SOT-223</p> |
|  <p>FDT459N Fairchild/ON Semiconductor MOSFET N-CH 30V 6.5A SOT-223</p> |  <p>FDT86102LZ AMI Semiconductor / ON Semiconductor MOSFET N-CH 100V 6.6A SOT-223</p> |  <p>FDT461N AMI Semiconductor / ON Semiconductor MOSFET N-CH 100V 0.54A SOT-223</p> |  <p>FDT458P-NL FAI FDT458P-NL FAI</p> |

heiße Teile

Mehr

| | | | | |
|----------------------|---------------|------------------|-----------------|---------------|
| 06032U1R9CAT2A | 2761021447 | AR7646-LF | ATMXT336S-MAUO | BA78M08FP-E2 |
| CX2016DB26000D0HFLC1 | DMN2112SN-7-F | ECH8310-TL | EL7158ISZ | FDT1600N10ALZ |
| FDT1600N10ALZ | FDT3N40TF | FDT3N40TF | FDT434P-NL | FDT439N-NL |
| FDT458P-NL | FDT55AN06LA0 | FDT86102LZ | FDT86102LZ | FDT86106LZ |
| FDT86106LZ | FDT86113LZ | FDT86113LZ | FDT86244 | FDT86244 |
| FDT86246 | FDT86246 | FDT86246L | FDT86246L | FDT86256 |
| FDT86256 | FQD6N60CTM | HV6810WG-G | IMP528EMA-T | INN2024K |
| LD025A3R3BAB2A | LM34910BSDX | LTST-C191TBKT-CA | MAX35103EHJ+T | MINI58ZDE |
| miniSMD110-2 | MJD31CRLG | PC847XIJ000F | SIR492DP-T1-GE3 | SM15T75A |
| SN75LBC174ADWR | SSM3K7002CFU | TPSY227M010P0200 | VI-2W4-CY | WM8350LGEB/V |

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